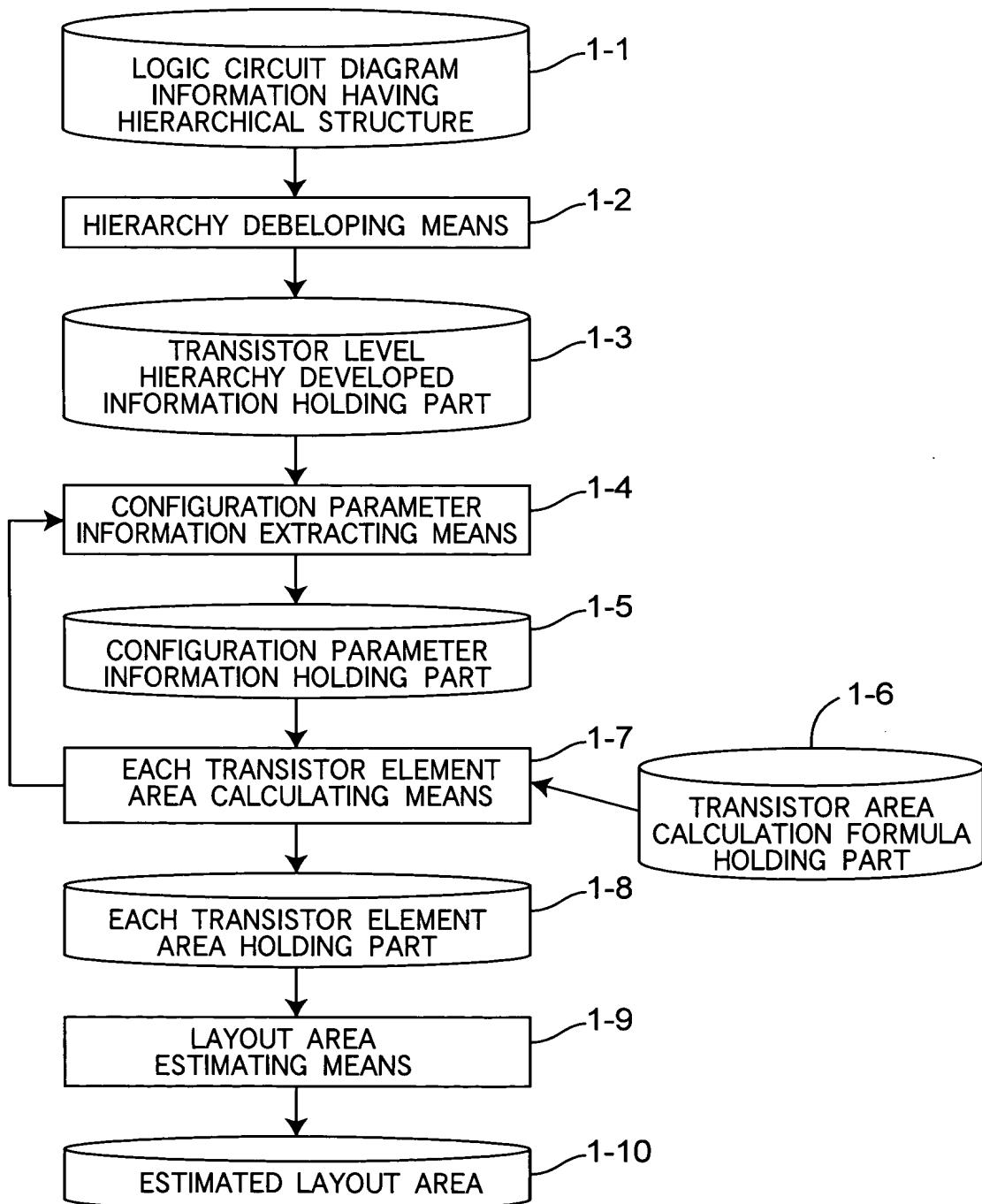
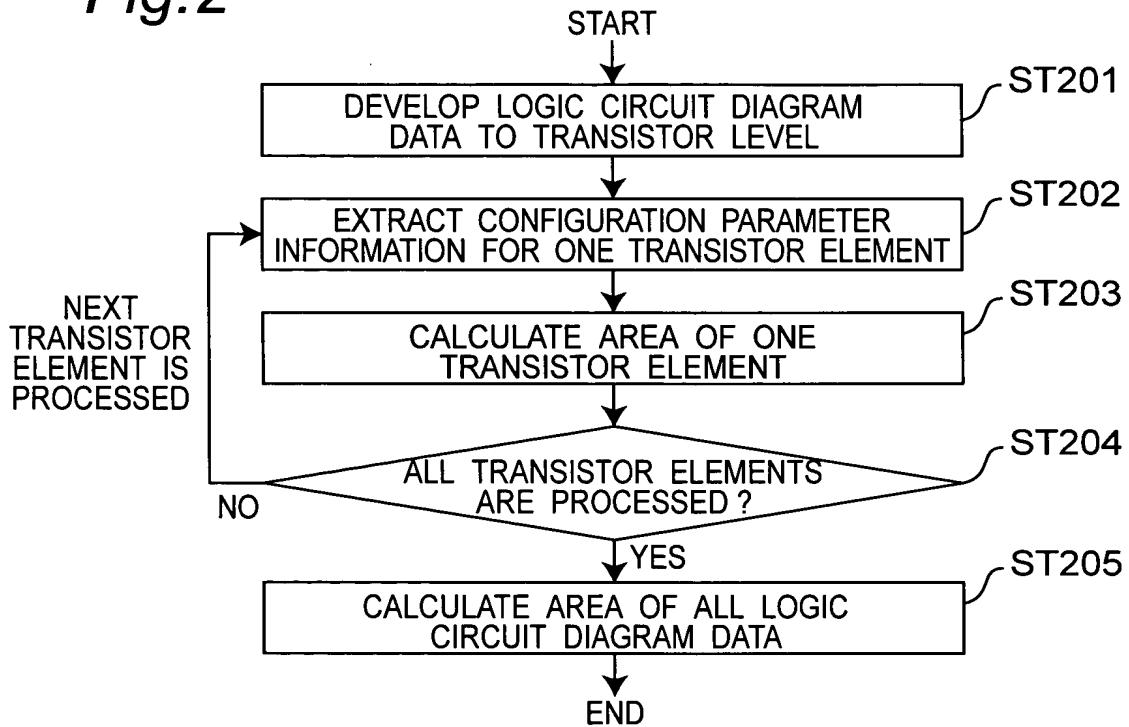


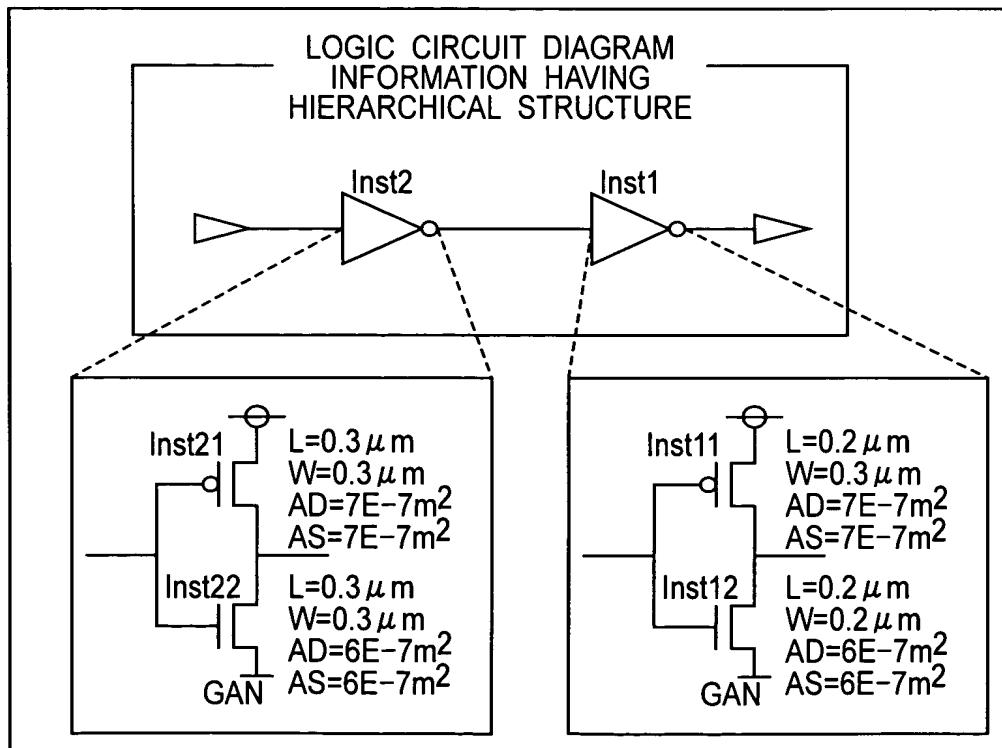
*Fig. 1*



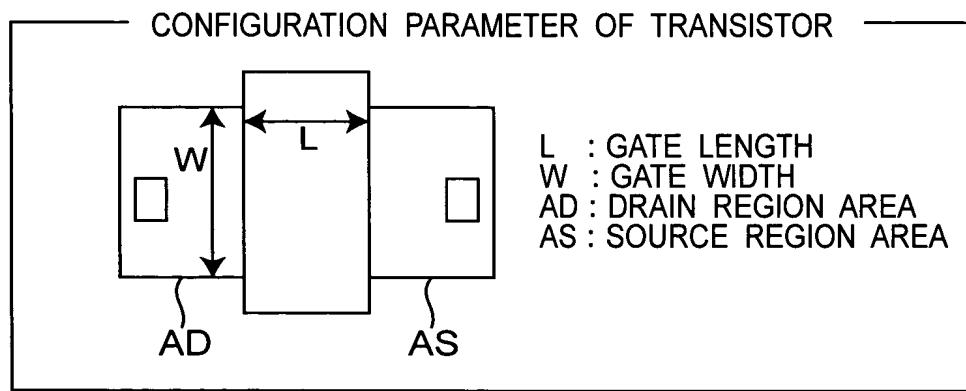
*Fig.2*



*Fig.3*



*Fig.4*

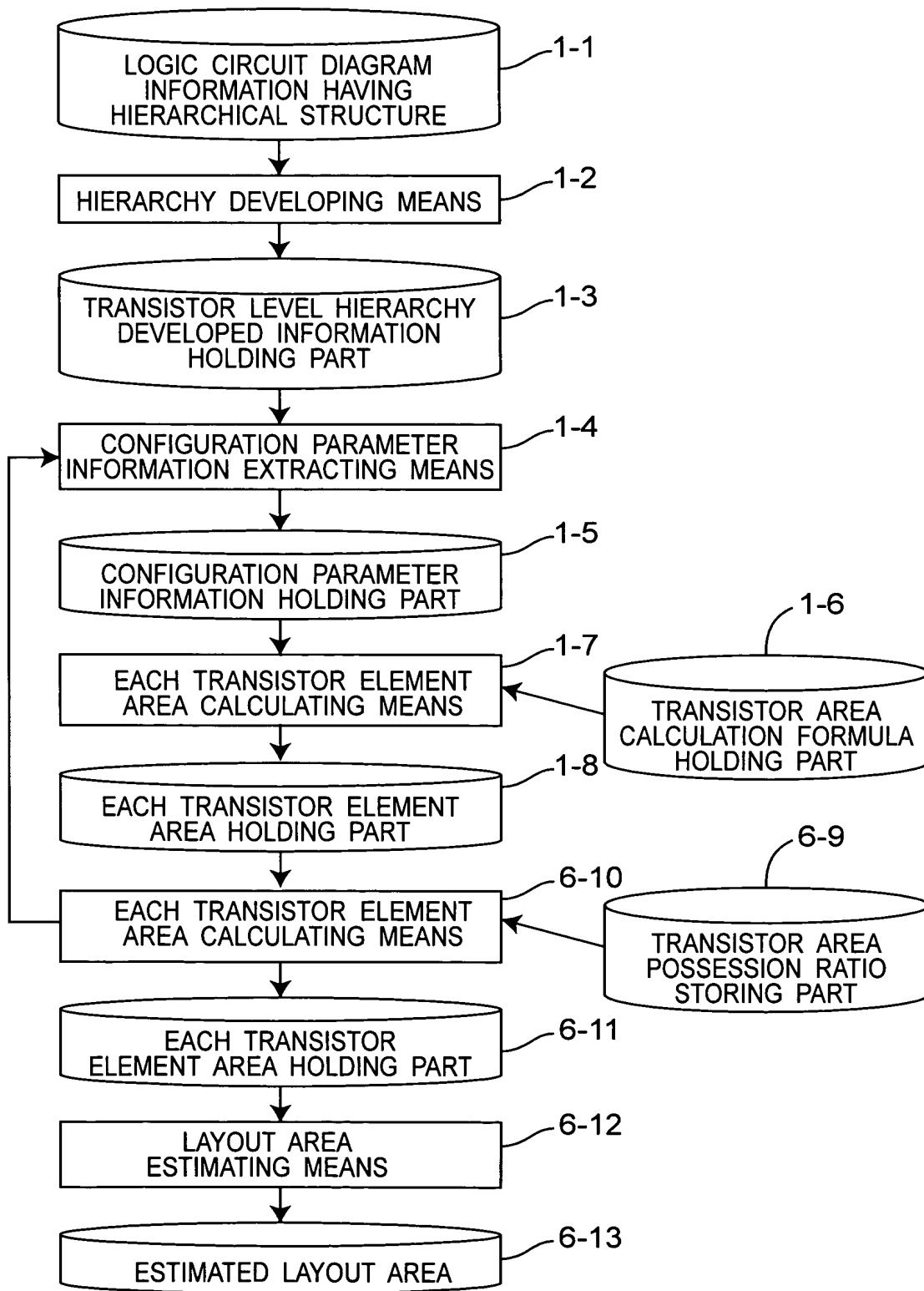


*Fig.5*

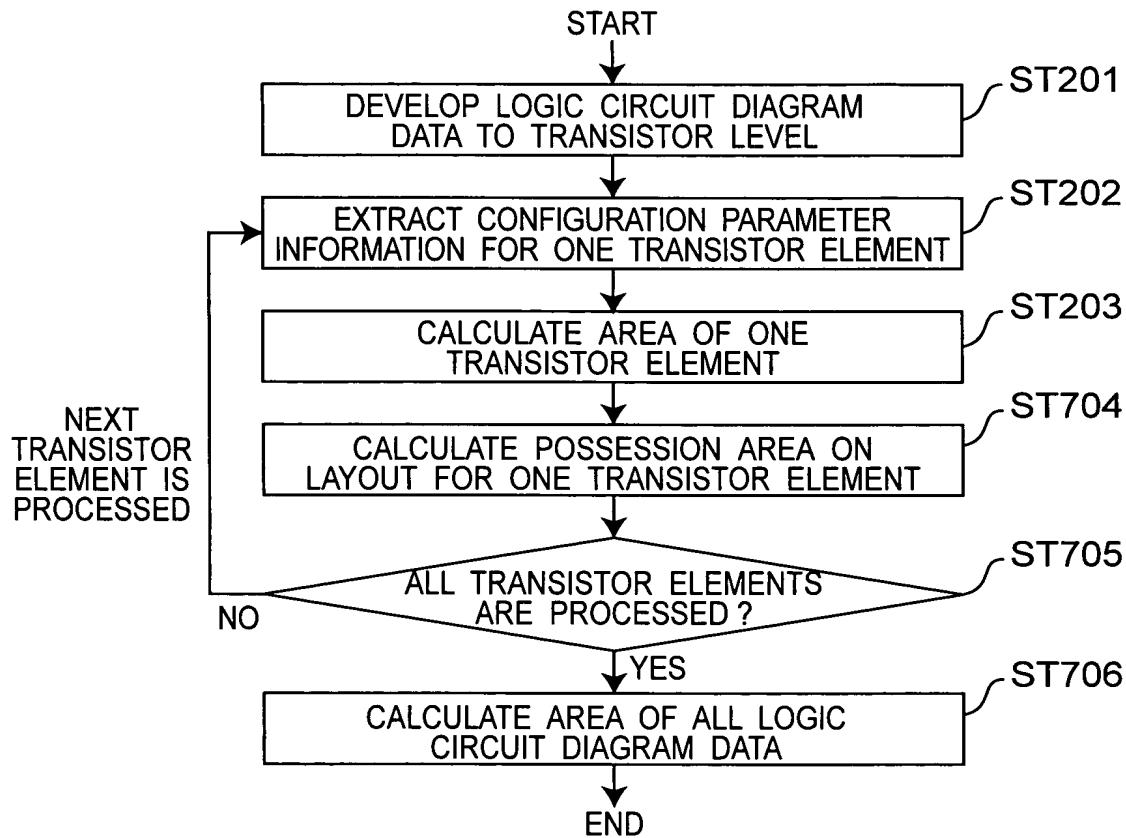
TRANSISTOR AREA CALCULATION  
FORMULA HOLDING PART

$$\text{ONE TRANSISTOR AREA} = L \times W + AD + AS$$

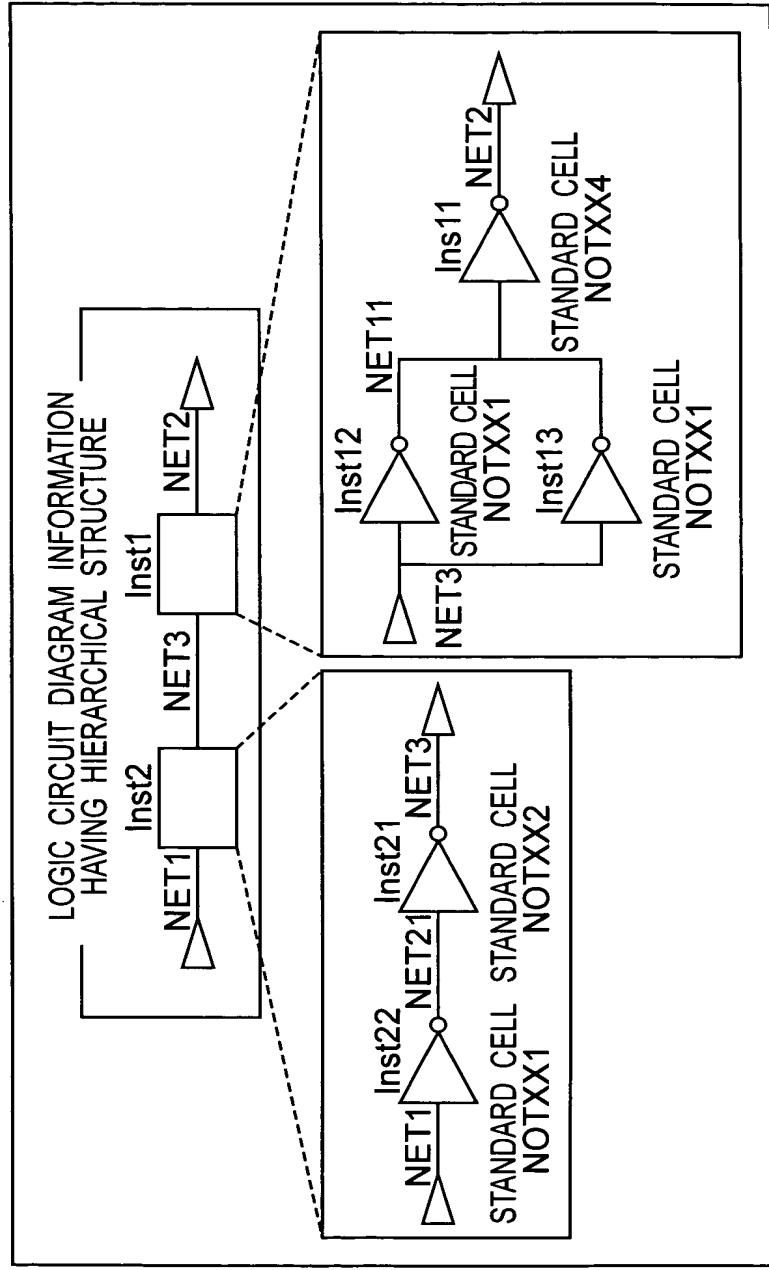
*Fig.6*



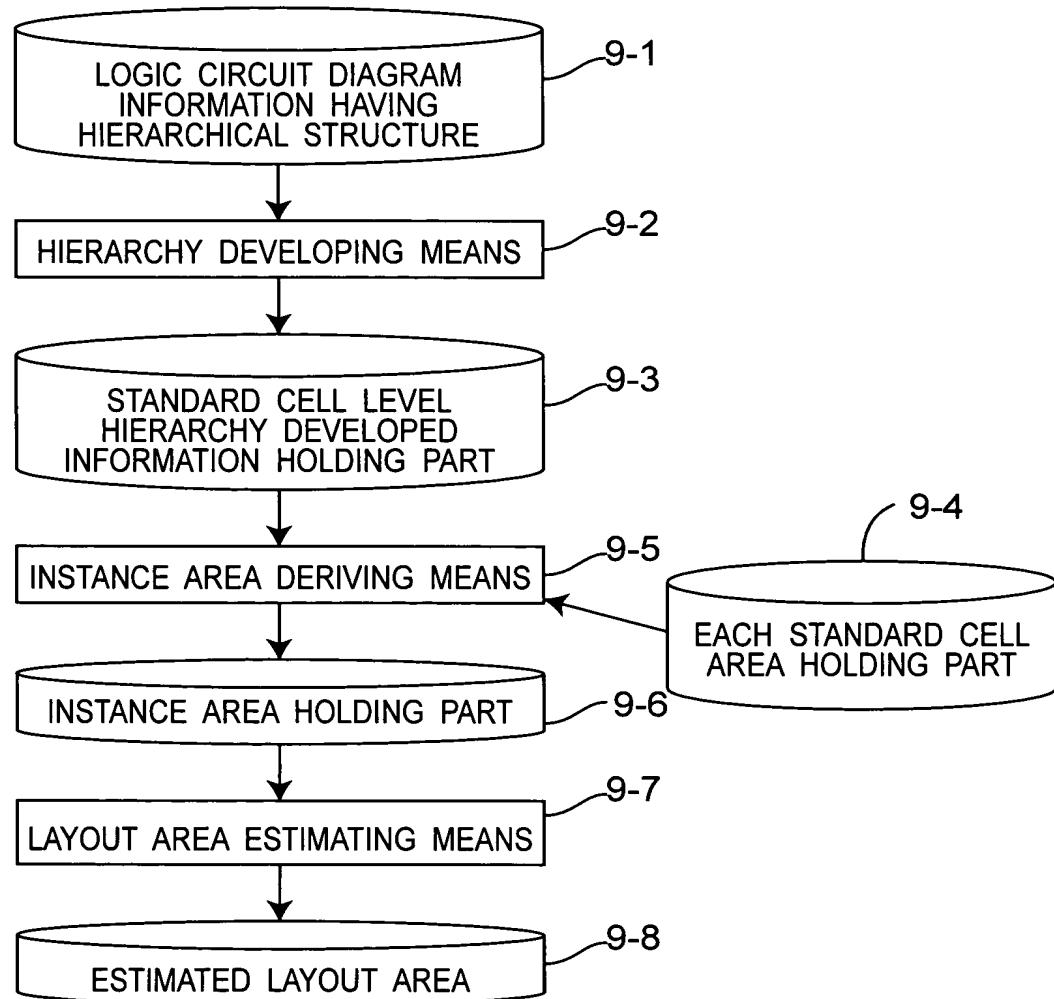
*Fig. 7*



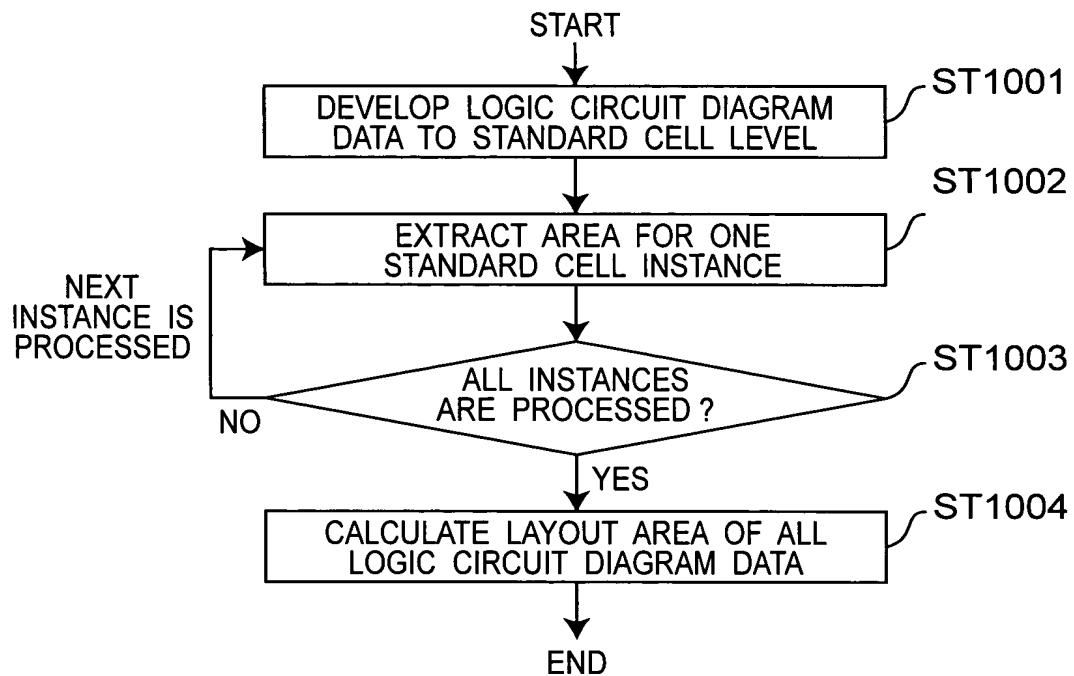
*Fig. 8*



*Fig.9*



*Fig.10*

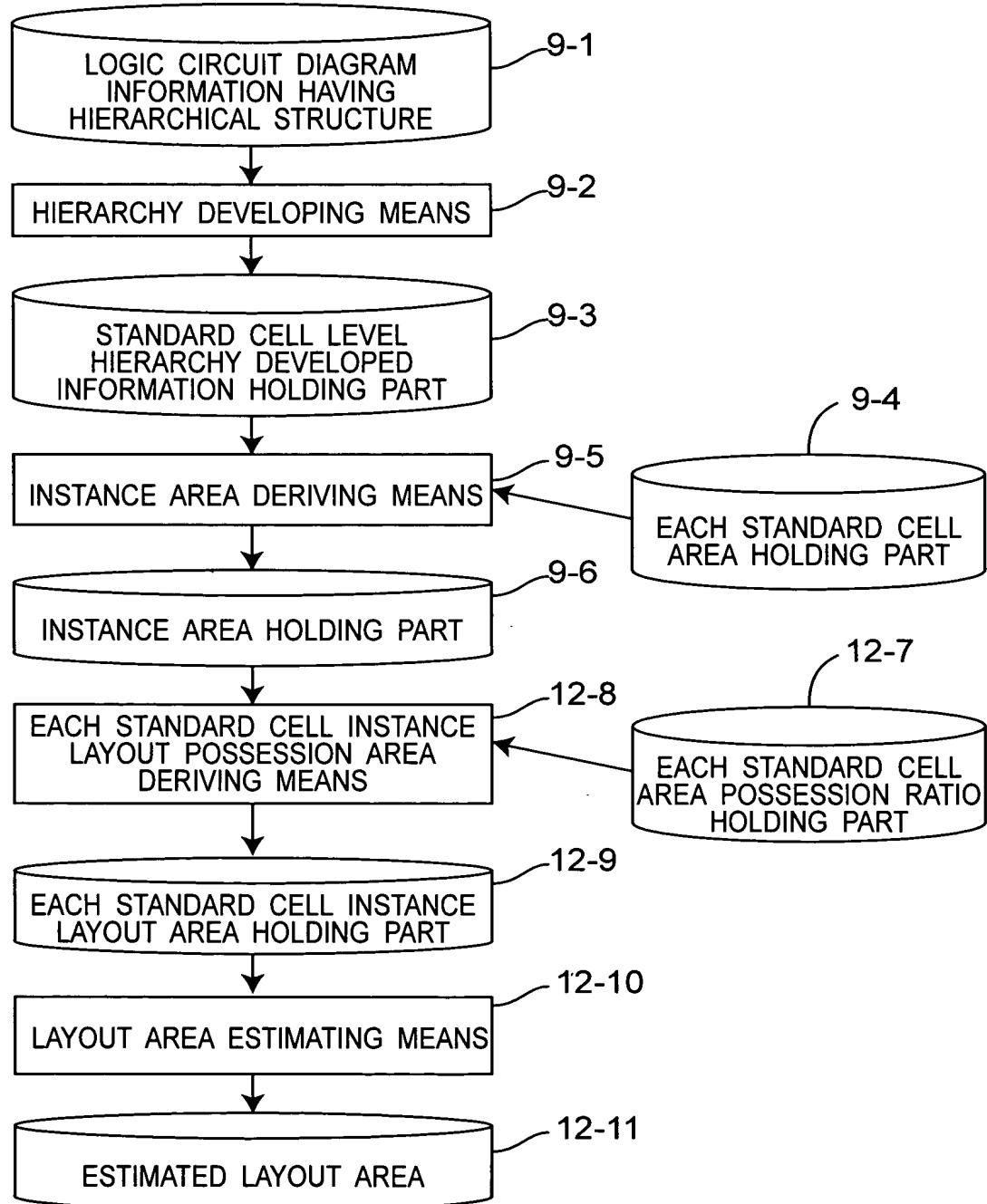


*Fig.11*

DEFINITION EXAMPLE OF EACH STANDARD CELL AREA HOLDING PART

NOTXX1	10E-8 $\mu\text{m}^2$
NOTXX2	20E-8 $\mu\text{m}^2$
NOTXX4	40E-8 $\mu\text{m}^2$
NOTXX8	80E-8 $\mu\text{m}^2$
:	:
:	:

*Fig. 12*



*Fig. 13*

DEFINITION EXAMPLE OF EACH STANDARD CELL AREA POSSESSION RATIO HOLDING PART

NOTXX1	0.8
NOTXX2	0.9
NOTXX4	0.9
NOTXX8	0.8
:	:
:	:

*Fig. 14*

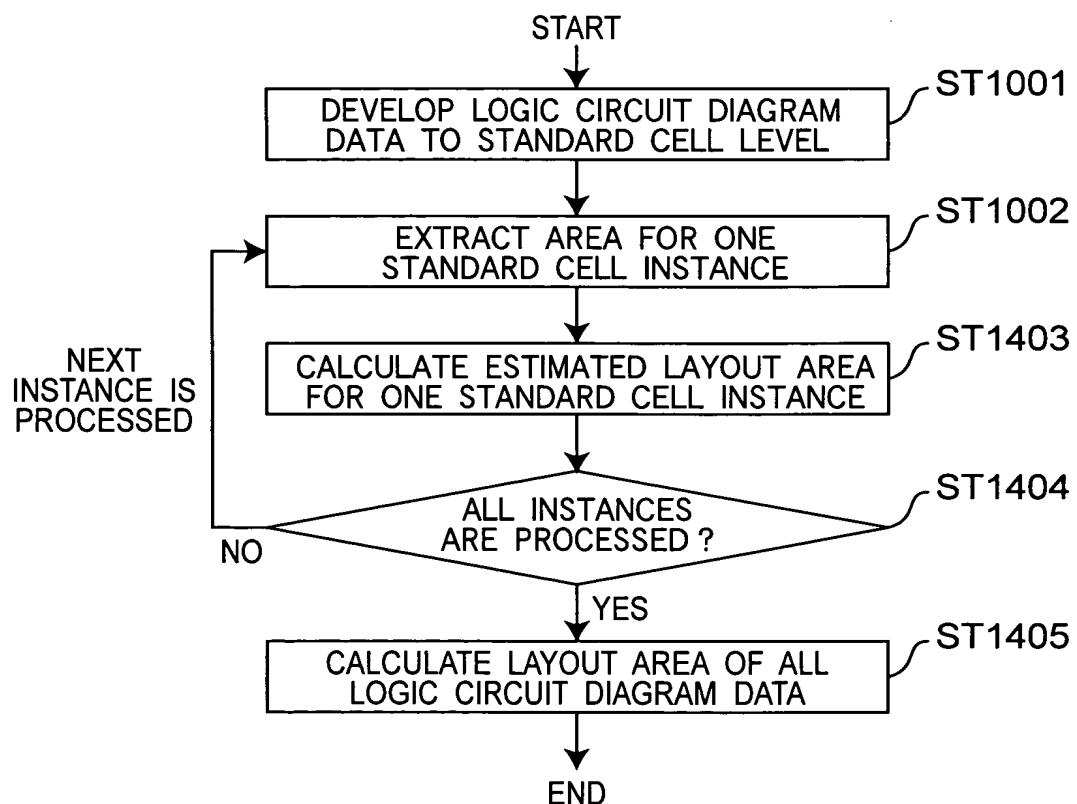
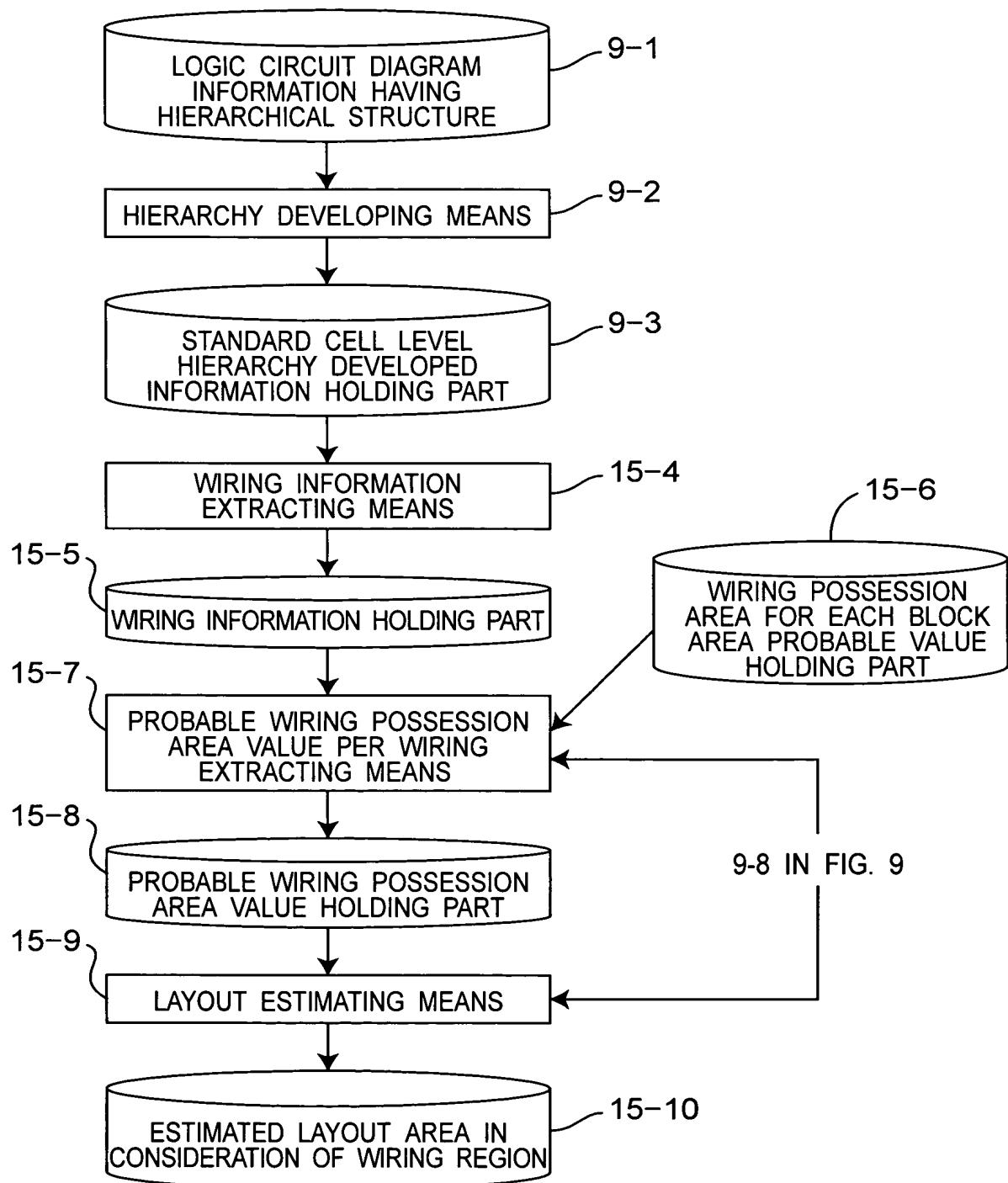
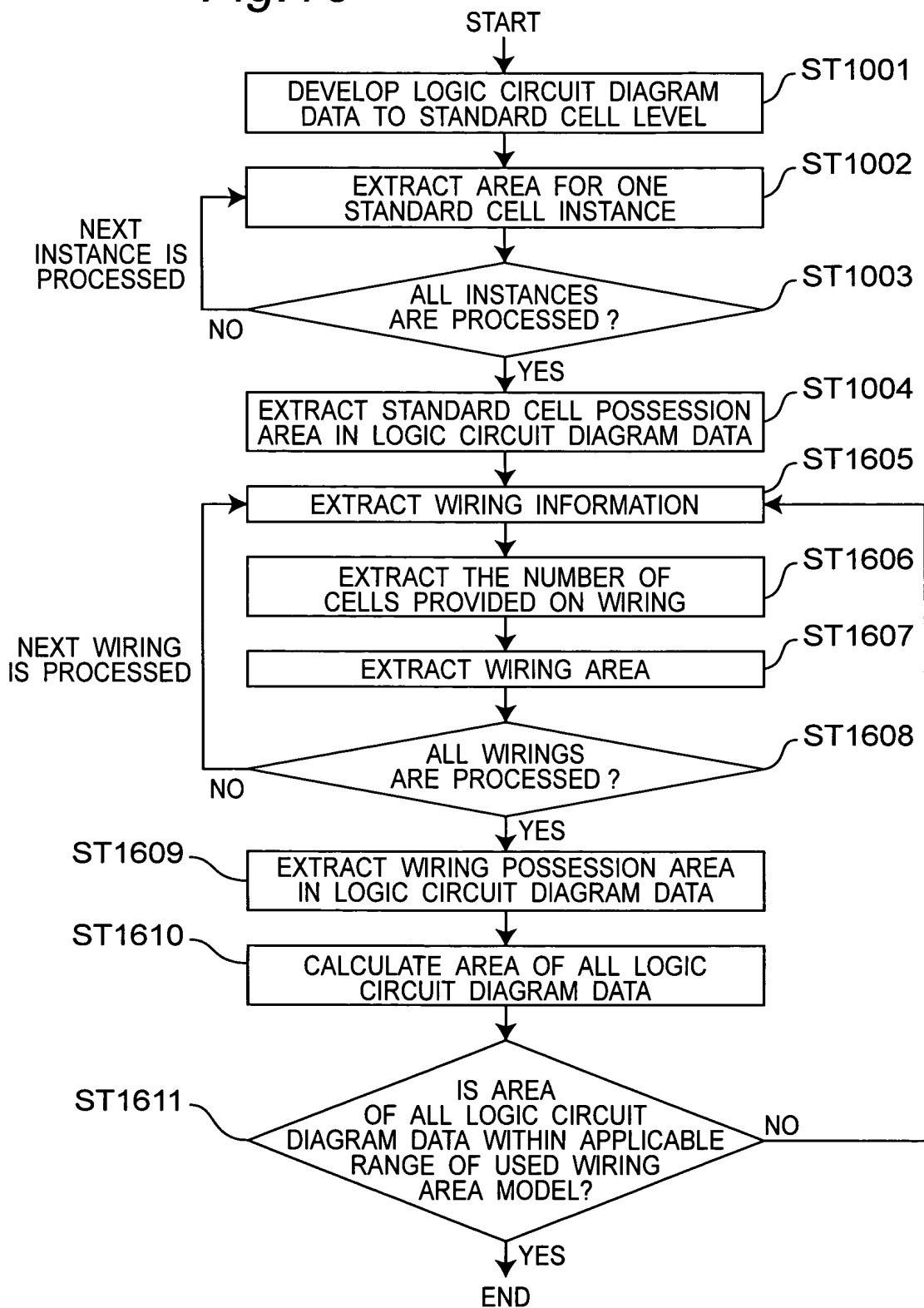


Fig. 15



*Fig. 16*



*Fig. 17*

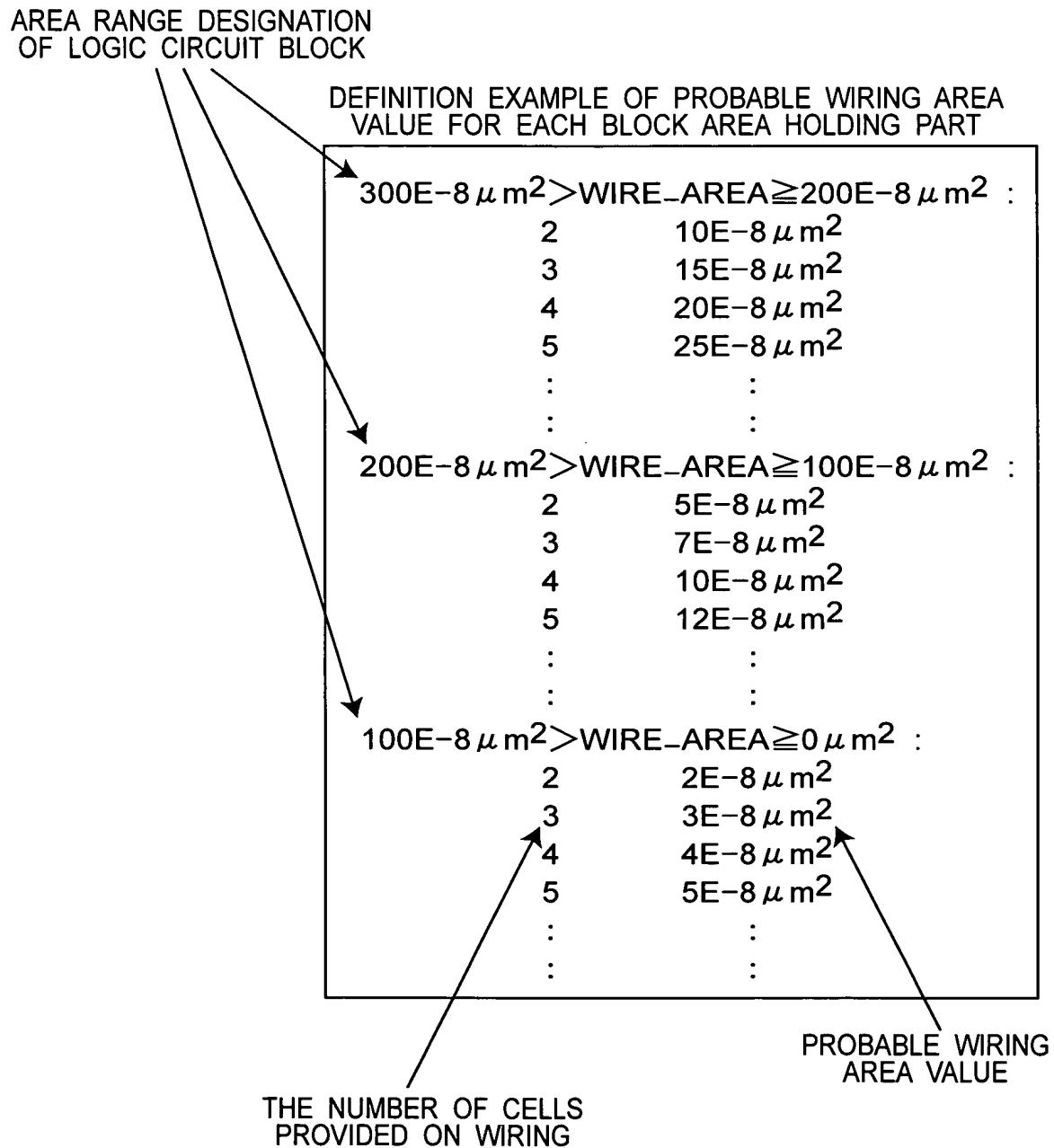


Fig. 18

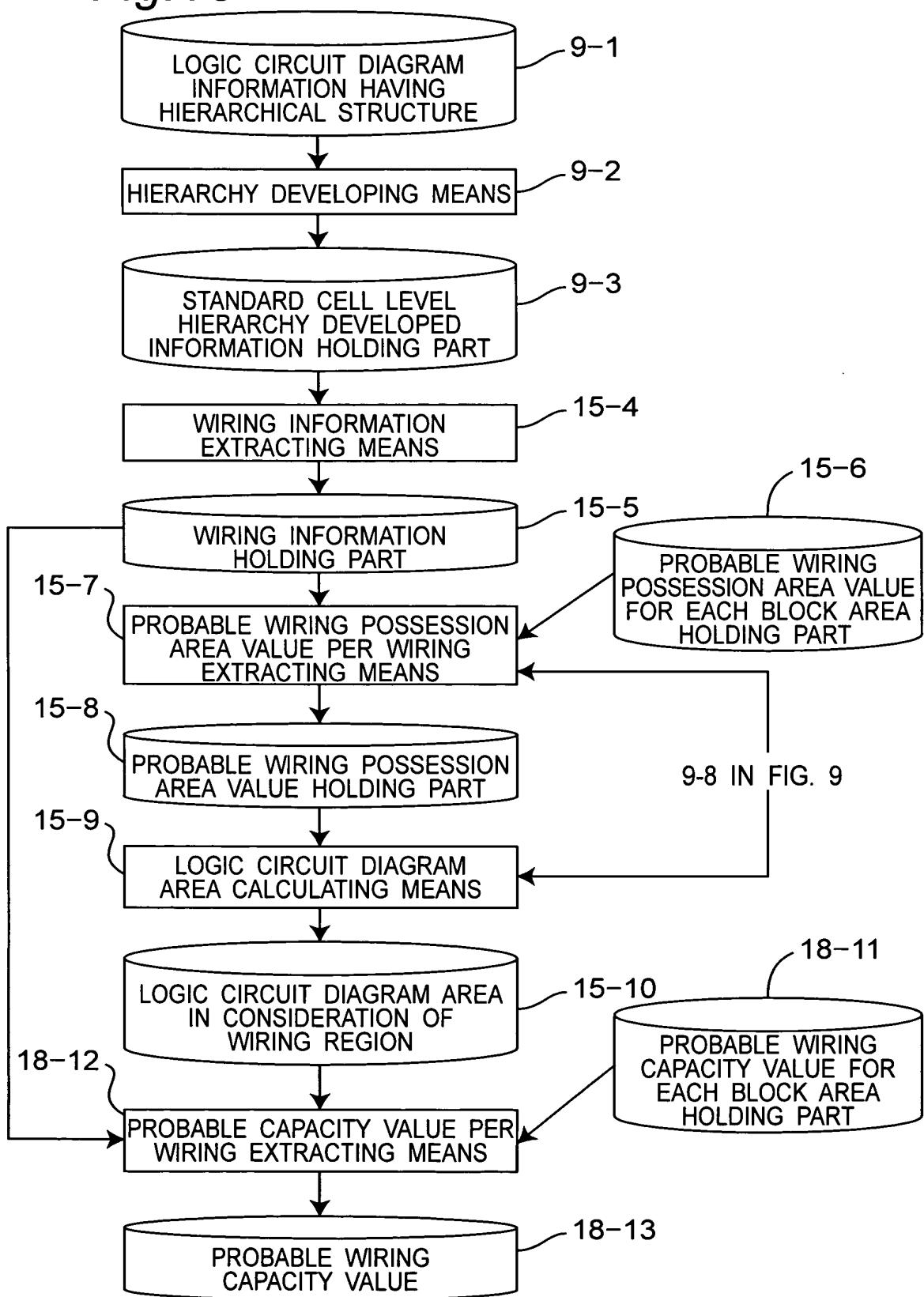
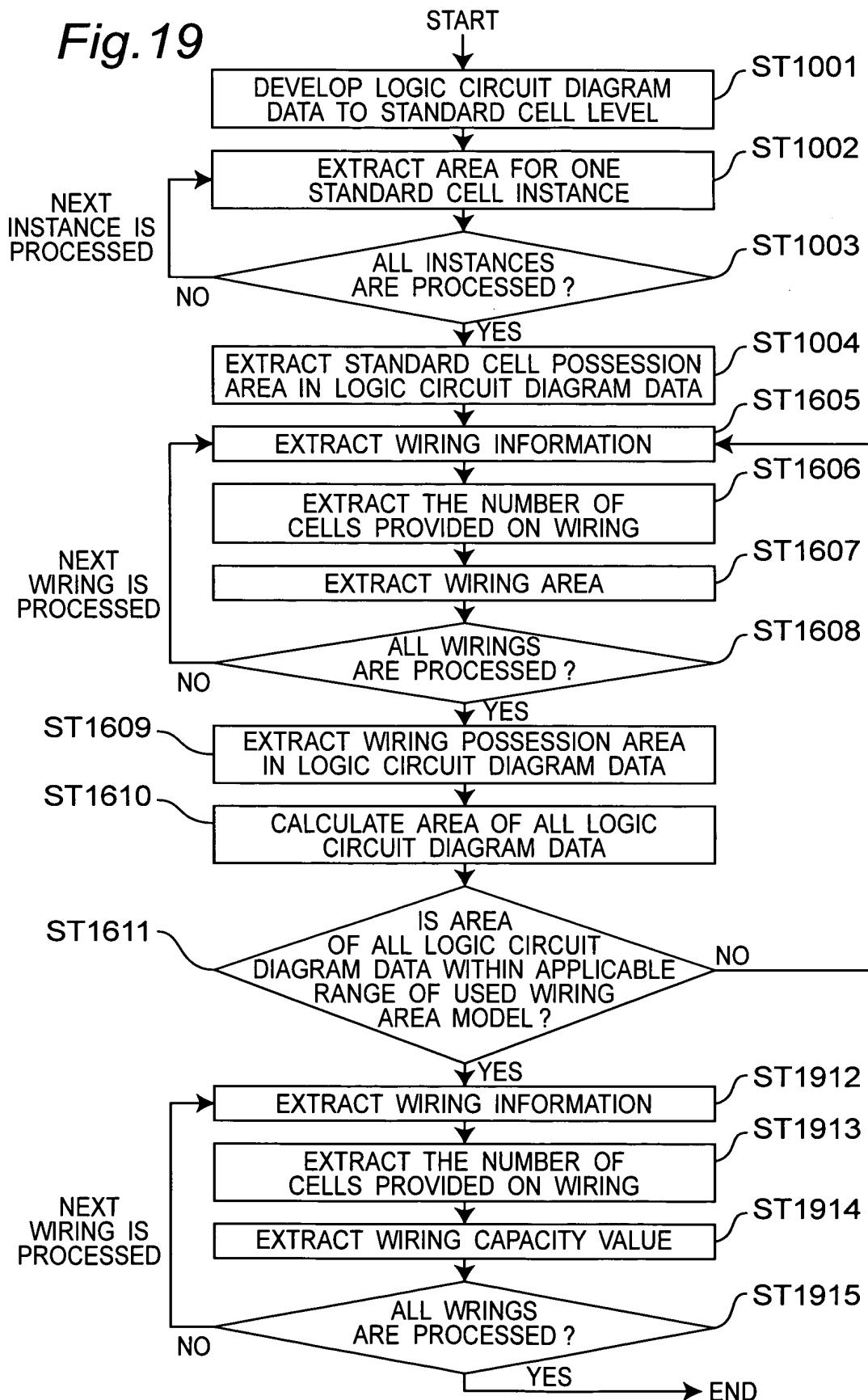


Fig. 19



*Fig.20*

AREA RANGE DESIGNATION  
OF LOGIC CIRCUIT BLOCK

DEFINITION EXAMPLE OF PROBABLE WIRING CAPACITY  
VALUE FOR EACH BLOCK AREA HOLDING PART

$300E-8 \mu m^2 > WIRE\_AREA \geq 200E-8 \mu m^2 :$

2	0.10pf
3	0.13pf
4	0.15pf
5	0.17pf
:	:
:	:

$200E-8 \mu m^2 > WIRE\_AREA \geq 100E-8 \mu m^2 :$

2	0.07pf
3	0.08pf
4	0.10pf
5	0.12pf
:	:
:	:

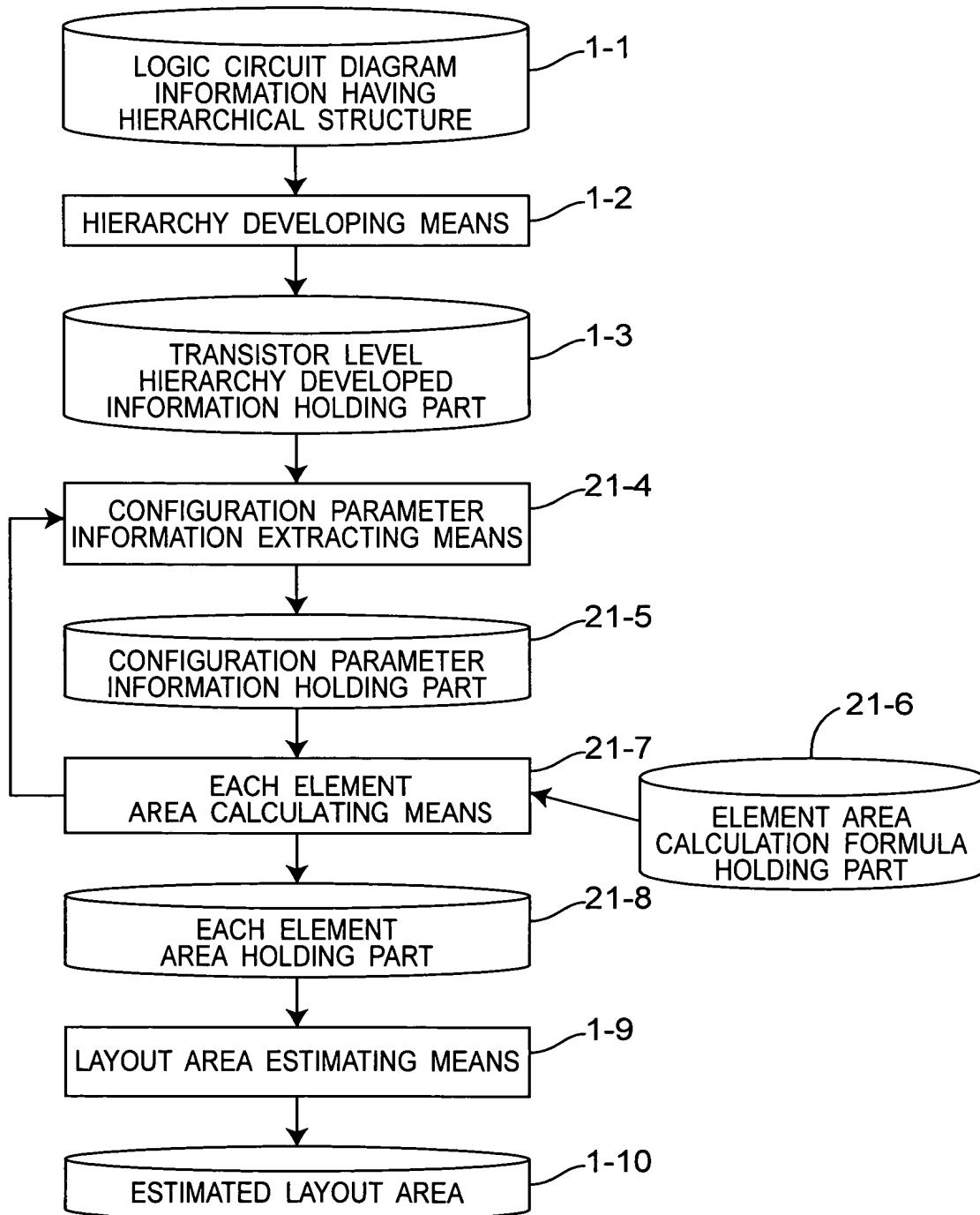
$100E-8 \mu m^2 > WIRE\_AREA \geq 0 \mu m^2 :$

2	0.03pf
3	0.04pf
4	0.05pf
5	0.06pf
:	:
:	:

THE NUMBER OF CELLS  
PROVIDED ON WIRING

PROBABLE WIRING  
AREA VALUE

Fig.21



*Fig.22*

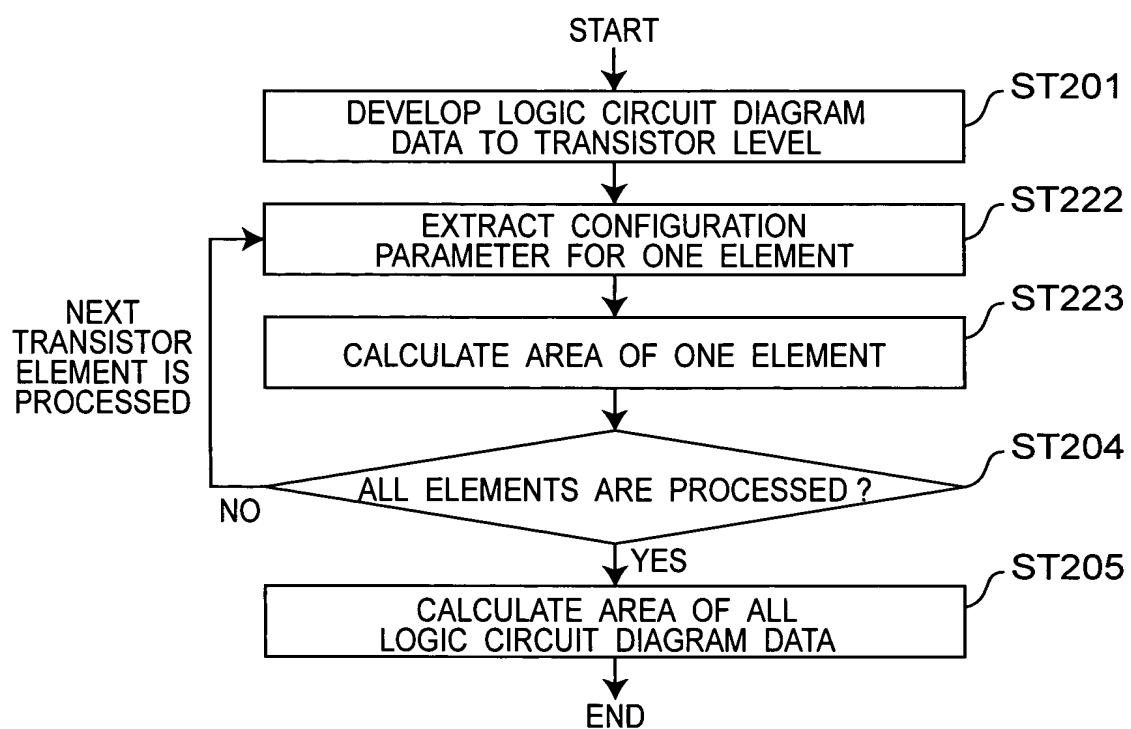
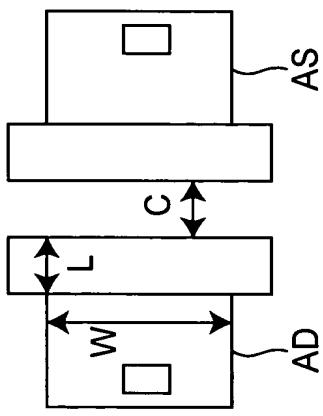


Fig.23

CONFIGURATION PARAMETER OF TRANSISTOR



PARAMETER OF RESISTANCE : RESISTANCE VALUE

PARAMETER OF CAPACITY : CAPACITY VALUE

Fig.24

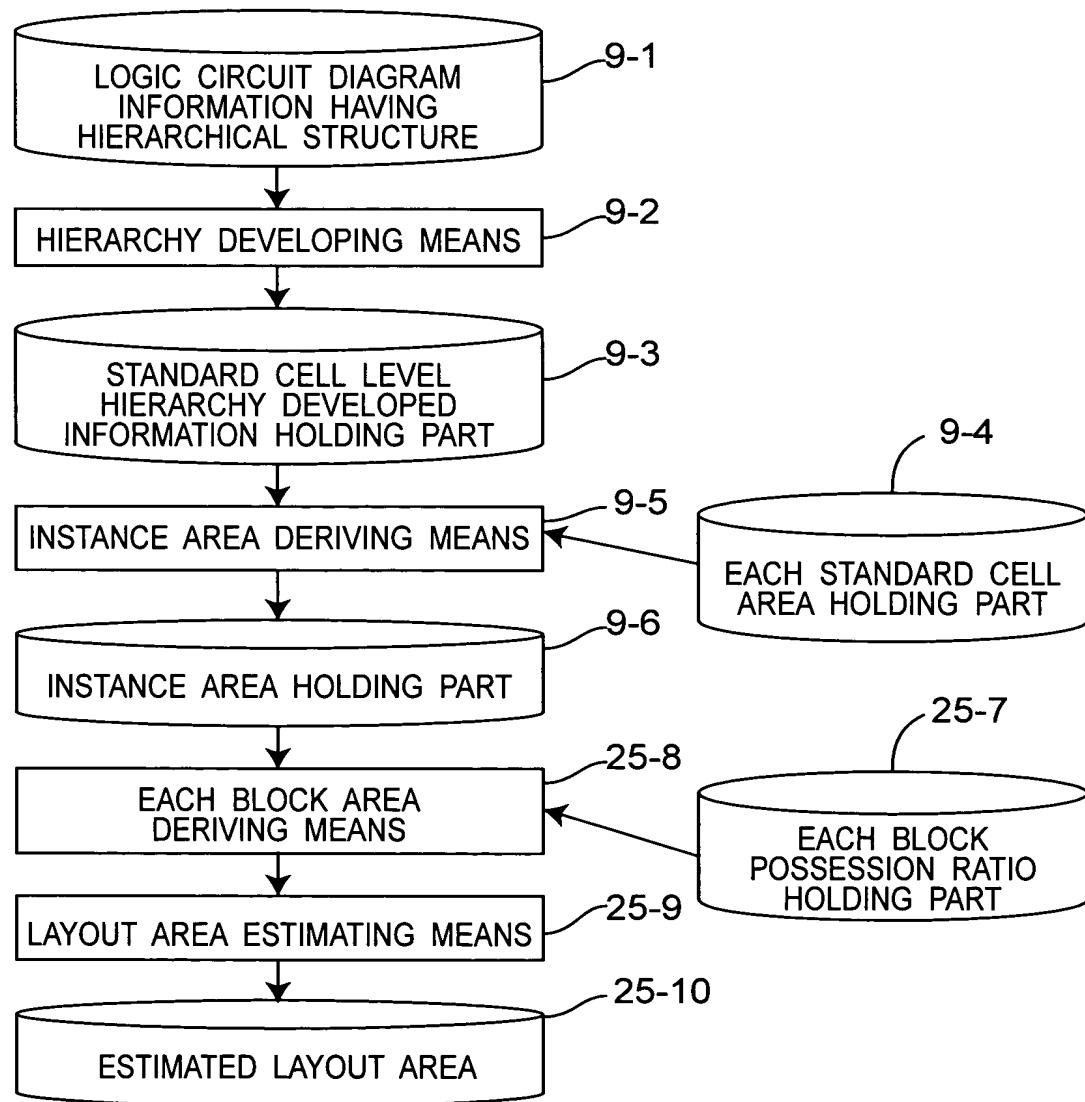
TRANSISTOR AREA CALCULATION FORMULA HOLDING PART

ONE TRANSISTOR AREA =  $L \times W \times M + AD + AS + D \times W$

AREA OF ONE RESISTANCE = [RESISTANCE VALUE] / [RESISTANCE VALUE PER UNIT LENGTH]  $\times$  [WIRING WIDTH]

AREA OF ONE CAPACITY = [CAPACITY VALUE] / [CAPACITY VALUE PER UNIT LENGTH]  $\times$  [WIRING WIDTH]

*Fig. 25*



*Fig.26*

